

Product Overview

N64S830HA: Serial SRAM Memory, 64-kb, 3.0 V

For complete documentation, see the data sheet.

The ON Semiconductor serial SRAM family includes several integrated memory devices including this 64 k serially accessed Static Random Access Memory, internally organized as 8 k words by 8 bits. The devices are designed and fabricated using advanced CMOS technology to provide both high-speed performance and low power. The devices operate with a single chip select (CS) input and use a simple Serial Peripheral Interface (SPI) serial bus. A single data in and data out line is used along with a clock to access data within the devices. The N64S830HA devices include a HOLD pin that allows communication to the device to be paused. While paused, input transitions will be ignored. The devices can operate over a wide temperature range of -40°C to +85°C and can be available in several standard package offerings.

Features

- 2.7 to 3.6 V power supply range
 - Very low standby current - as low as 1 μ A
 - Very low operating current - as low as 3 mA
 - Flexible operating modes: word read and write, page mode (32 word page), and burst mode (full array)
 - 8 K x 8 bit organization
 - Simple memory control: single chip select (CS), serial input (SI) and serial output (SO)
 - Self timed write cycles
 - Built-in write protection (CS high)
 - HOLD pin for pausing communication
 - High reliability - unlimited write cycles
- For more features, see the data sheet

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Type	Density	Organization (bits)	f _{cycle} Max (MHz)	V _{CC} Min (V)	V _{CC} Max (V)	I _{standby} Typ (μ A)	Package Type
N64S830HAS22I	0.8	Pb-free Halide free non AEC-Q and PPAP	Active	Serial	64 kb	8k x 8	20	2.7	3.6	1	SOIC-8
N64S830HAT22I	0.8	Pb-free Halide free non AEC-Q and PPAP	Active	Serial	64 kb	8k x 8	20	2.7	3.6	1	TSSOP-8

For more information please contact your local sales support at www.onsemi.com.

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